Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.455$ V at $I_F = 5$ A

NTST30100CTG, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

Typical Applications

- SNOT RECONNERORIES • Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



ON Semiconductor® www.onsemi.com **PIN CONNECTIONS** 10 **I2PAK** TO 220AB CASE 221A CASE 418D STYLE 6 STYLE 3

TO-220FP CASE 221AH

D2PAK CASE 418AJ

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

1

MAXIMUM RATINGS

Rating			Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	100	V
Average Rectified Forward Current (Rated V_R , T_C = 115°C)	Per device Per diode	I _{F(AV)}	30 15	A
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz, T _C = 110°C)	Per device Per diode	I _{FRM}	60 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I _{FSM}	160	A
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T _{stg}	-40 to +150	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality EN DE should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

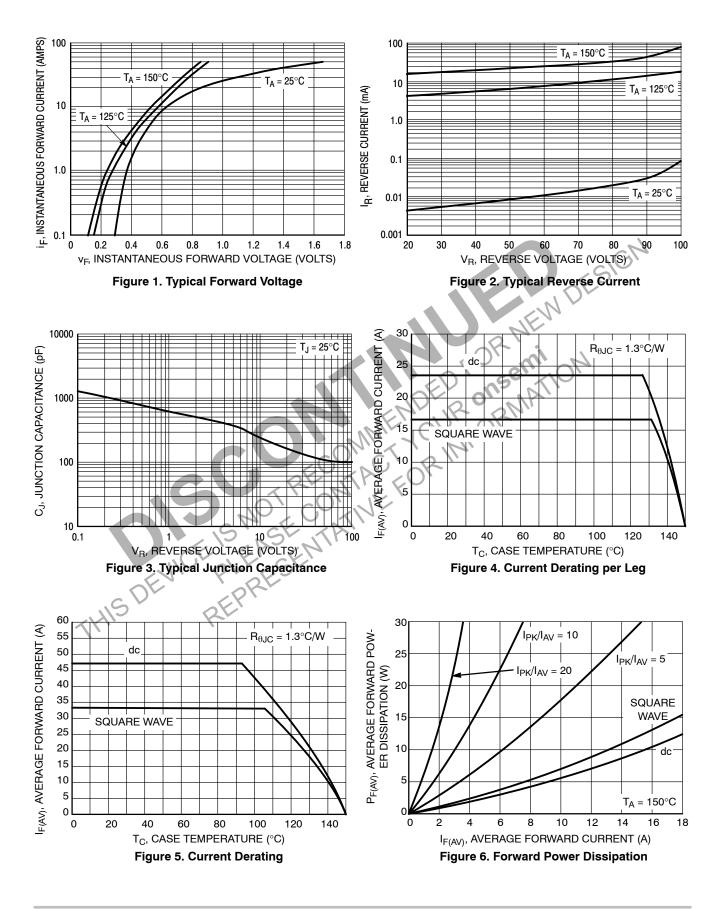
Rating	Symbol	NTST30100CTG, NTSB30100CT-1G	NTSB30100CTG	NTSJ30100CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$R_{ heta JC} R_{ heta JA}$	2.5 70	1.14 46.6	4.09 105	°C/W °C/W
ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)					

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted

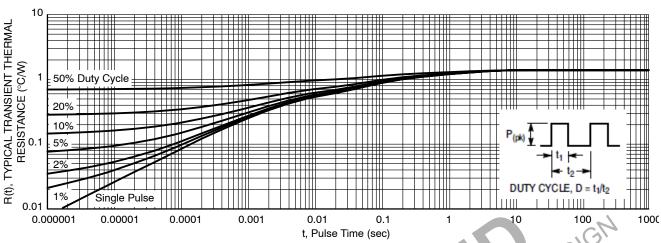
Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1)	٧ _F			V
$(I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.516	-	
$(I_F = 7.5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.576	-	
$(I_F = 15 \text{ A}, T_J = 25^{\circ}\text{C})$		0.734	0.85	
(I _F = 5 A, T _J = 125°C)		0.455	_	
$(I_F = 7.5 \text{ A}, T_J = 125^{\circ}\text{ G})$		0.522	-	
(I _F = 15 A, T _J = 125°C)		0.627	0.68	
Maximum Instantaneous Reverse Current (Note 1)	I _B			
$(V_{R} = 70 \text{ V}, T_{y} = 25^{\circ}\text{C})$		7.2		μΑ
(V _R = 70 V, T _J = 125°C)		8.0		mA
Detect de Veltage T (0590)		ee.	500	
(Rated dc Voltage, $T_J = 25^{\circ}C$) (Rated dc Voltage, $T_J = 125^{\circ}C$)		65 20	500 35	μA m A
(Frated up voltage, 1) = 125 G		20	- 55	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle $\leq 2.0\%$

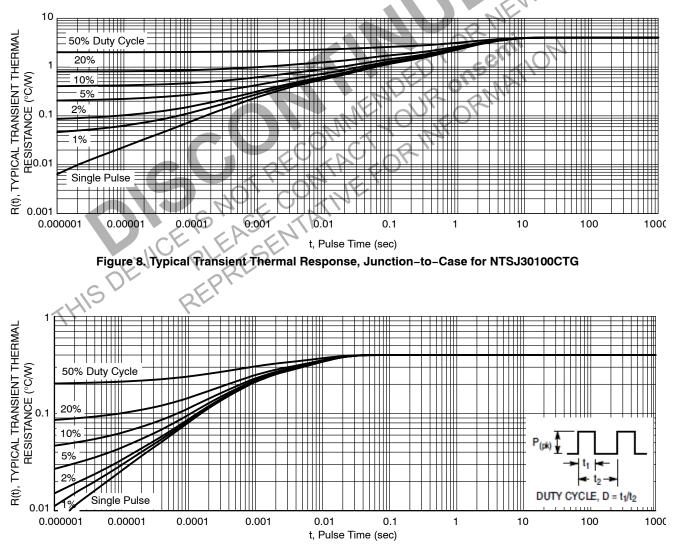


TYPICAL CHARACTERISITICS



TYPICAL CHARACTERISITICS



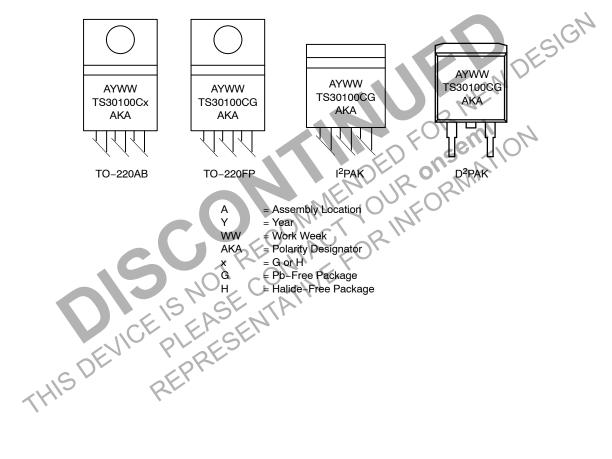




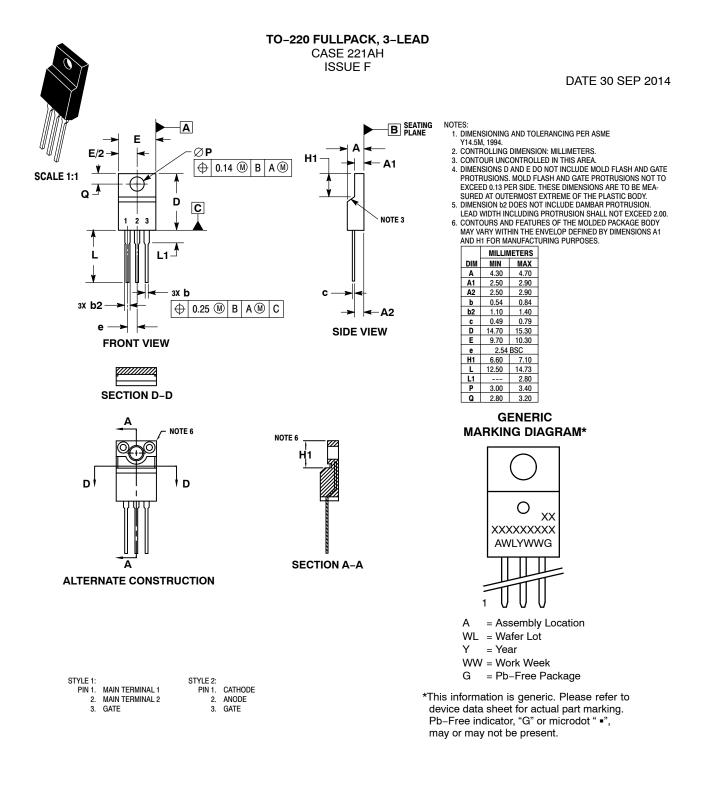
ORDERING INFORMATION

Device Package		Shipping
NTST30100CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTSB30100CT-1G	l ² PAK (Pb–Free)	50 Units / Rail
NTSJ30100CTG	TO-220FP (Halide-Free)	50 Units / Rail
NTSB30100CTG	D ² PAK (Pb-Free)	50 Units / Rail
NTSB30100CTT4G	D ² PAK (Pb–Free)	800 / Tape & Reel

MARKING DIAGRAMS



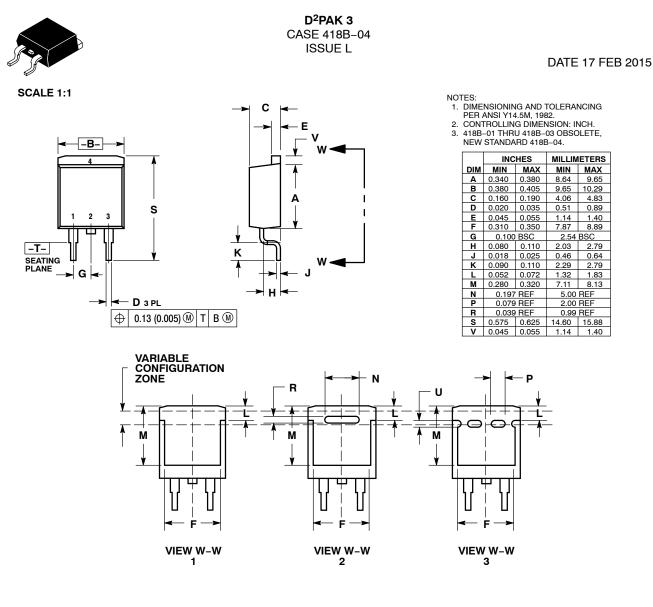
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STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. GATE	PIN 1. CATHODE	PIN 1. NO CONNECT
2. COLLECTOR	2. DRAIN	2. CATHODE	2. COLLECTOR	2. ANODE	2. CATHODE
3. EMITTER	SOURCE	ANODE	3. EMITTER	CATHODE	3. ANODE
4. COLLECTOR	4. DRAIN	CATHODE	4. COLLECTOR	4. ANODE	4. CATHODE

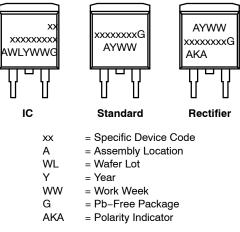
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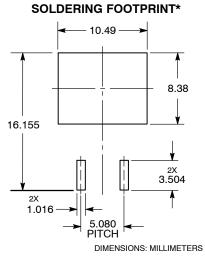
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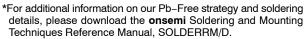
DATE 17 FEB 2015

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.





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